



# 20 $\mu$ A Maximum, Rail-to-Rail I/O, Zero Input, Crossover Distortion Amplifiers

Preliminary Technical Data

**AD8508**

## FEATURES

PSRR: 100 dB minimum

CMRR: 105 dB typical

Very low supply current: 20  $\mu$ A per amp maximum

1.8 V to 5 V single-supply or  $\pm 0.9$  V to  $\pm 2.5$  V dual-supply operation

Rail-to-rail input and output

2.5 mV offset voltage maximum

Very low input bias current: 1 pA typical

## APPLICATIONS

Pressure and position sensors

Remote security

Bio sensors

IR thermometers

Battery-powered consumer equipment

Hazard detectors

## GENERAL DESCRIPTION

The AD8508 is a quad micropower amplifiers featuring rail-to-rail input and output swings while operating from a 1.8 V to 5 V single or from  $\pm 0.9$  V to  $\pm 2.5$  V dual power supply.

Using a novel circuit technology, these low cost amplifiers offer zero crossover distortion (excellent PSRR and CMRR performance) and very low bias current, while operating with a supply current of less than 20  $\mu$ A per amplifier. This amplifier offers the lowest noise in its power class.

This combination of features makes the AD8508 amplifiers ideal choices for battery-powered applications because they minimize errors due to power supply voltage variations over the lifetime of the battery and maintain high CMRR even for a rail-to-rail input op amp.

## PIN CONFIGURATION

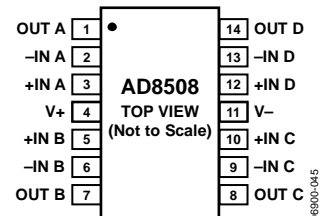


Figure 1. 14-Lead TSSOP (RU-14)

Remote battery-powered sensors, handheld instrumentation and consumer equipment, hazard detection (for example, smoke, fire, and gas), and patient monitors can benefit from the features of the AD8508 amplifiers.

The AD8508 are specified for both the industrial temperature range of  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$  and the extended industrial temperature range of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ . The AD8508 quad amplifiers are available in the 14-lead TSSOP package.

## Rev. PrA

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One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.  
Tel: 781.329.4700 [www.analog.com](http://www.analog.com)

Fax: 781.461.3113

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## SPECIFICATIONS

## ELECTRICAL CHARACTERISTICS—5 V OPERATION

$V_{SY} = 5\text{ V}$ ,  $V_{CM} = V_{SY}/2$ ,  $T_A = 25^\circ\text{C}$ ,  $R_L = 100\text{ k}\Omega$  to GND, unless otherwise noted.

Table 1.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	$V_{OS}$	$0\text{ V} \leq V_{CM} \leq 5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	2.5	mV
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		1	10	pA
					100	pA
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	5	pA
					50	pA
					130	pA
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		5	V
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	90	105		dB
			90			dB
			85			dB
Large Signal Voltage Gain	$A_{VO}$	$0.05\text{ V} \leq V_{OUT} \leq 4.95\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	105	120		dB
			100			dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2		$\mu\text{V}/^\circ\text{C}$
Input Capacitance Differential Mode	$C_{DIFF}$			3		pF
Input Capacitance Common Mode	$C_{CM}$			4.2		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$R_L = 100\text{ k}\Omega$ to GND $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	4.98	4.99		V
			4.98			V
			4.9	4.95		V
			4.9			V
Output Voltage Low	$V_{OL}$	$R_L = 100\text{ k}\Omega$ to $V_{SY}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2	5	mV
					5	mV
				10	25	mV
					30	mV
Short-Circuit Limit	$I_{SC}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		$\pm 55$		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 1.8\text{ V}$ to $5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	100	110		dB
			100			dB
			95			dB
Supply Current per Amplifier	$I_{SY}$	$V_{OUT} = V_{SY}/2$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		15	20	$\mu\text{A}$
					25	$\mu\text{A}$
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 100\text{ k}\Omega$ , $C_L = 10\text{ pF}$ , $G = 1$		13		$\text{mV}/\mu\text{s}$
Gain Bandwidth Product	GBP	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		95		kHz
Phase Margin	$\Phi_M$	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		60		Degrees
NOISE PERFORMANCE						
Voltage Noise	$e_n$ p-p	$f = 0.1\text{ Hz}$ to $10\text{ Hz}$		2.8		$\mu\text{V}$ p-p
Voltage Noise Density	$e_n$	$f = 1\text{ kHz}$		45		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	$i_n$	$f = 1\text{ kHz}$		15		$\text{fA}/\sqrt{\text{Hz}}$

**ELECTRICAL CHARACTERISTICS—1.8 V OPERATION**

$V_{SY} = 1.8\text{ V}$ ,  $V_{CM} = V_{SY}/2$ ,  $T_A = 25^\circ\text{C}$ ,  $R_L = 100\text{ k}\Omega$  to GND, unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>INPUT CHARACTERISTICS</b>						
Offset Voltage	$V_{OS}$	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	2.5	mV
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		1	10	pA
					100	pA
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	5	pA
					50	pA
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		1.8	V
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$	85	100		dB
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	85			dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	80			dB
Large Signal Voltage Gain	$A_{VO}$	$0.05\text{ V} \leq V_{OUT} \leq 1.75\text{ V}$	95	115		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	95			dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2.5		$\mu\text{V}/^\circ\text{C}$
Input Capacitance Differential Mode	$C_{DIFF}$			3		pF
Input Capacitance Common Mode	$C_{CM}$			4.2		pF
<b>OUTPUT CHARACTERISTICS</b>						
Output Voltage High	$V_{OH}$	$R_L = 100\text{ k}\Omega$ to GND	1.78	1.79		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.78			V
		$R_L = 10\text{ k}\Omega$ to GND	1.65	1.75		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.65			V
Output Voltage Low	$V_{OL}$	$R_L = 100\text{ k}\Omega$ to $V_{SY}$		2	5	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			5	mV
		$R_L = 10\text{ k}\Omega$ to $V_{SY}$		12	25	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			25	mV
Short-Circuit Limit	$I_{SC}$			$\pm 6.5$		mA
<b>POWER SUPPLY</b>						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 1.8\text{ V}$ to 5 V	100	110		dB
		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	100			dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	95			dB
Supply Current per Amplifier	$I_{SY}$	$V_{OUT} = V_{SY}/2$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		16.5	20	$\mu\text{A}$
					25	$\mu\text{A}$
<b>DYNAMIC PERFORMANCE</b>						
Slew Rate	SR	$R_L = 100\text{ k}\Omega$ , $C_L = 10\text{ pF}$ , $G = 1$		13		$\text{mV}/\mu\text{s}$
Gain Bandwidth Product	GBP	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		95		kHz
Phase Margin	$\Phi_M$	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		60		Degrees
<b>NOISE PERFORMANCE</b>						
Voltage Noise	$e_n$ p-p	$f = 0.1\text{ Hz}$ to 10 Hz		2.8		$\mu\text{V}$ p-p
Voltage Noise Density	$e_n$	$f = 1\text{ kHz}$		45		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	$i_n$	$f = 1\text{ kHz}$		15		$\text{fA}/\sqrt{\text{Hz}}$

## ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
Supply Voltage	5.5 V
Input Voltage	$\pm V_{SY} \pm 0.1$ V
Input Current <sup>1</sup>	$\pm 10$ mA
Differential Input Voltage <sup>2</sup>	$\pm V_{SY}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	-65°C to +150°C
Operating Temperature Range	-40°C to +125°C
Junction Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

<sup>1</sup> Input pins have clamp diodes to the supply pins. Input current should be limited to 10 mA or less whenever the input signal exceeds the power supply rail by 0.5 V.

<sup>2</sup> Differential input voltage is limited to 5 V or the supply voltage, whichever is less.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL RESISTANCE

$\theta_{JA}$  is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages. This was measured using a standard two-layer board.

Table 4. Thermal Resistance

Package Type	$\theta_{JA}$	$\theta_{JC}$	Unit
8-Lead MSOP (RM-8)	190	44	°C/W
14-Lead TSSOP (RU-14)	180	35	°C/W

## ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.